

R-C Thermal Model Parameters

DESCRIPTION

The parametric values in the R-C thermal model have been derived using curve-fitting techniques. These techniques are described in "[A Simple Method of Generating Thermal Models for a Power MOSFET](#)"[1]. When implemented in P-Spice, these values have matching characteristic curves to the Single Pulse Transient Thermal Impedance curves for the MOSFET.

R-C values for the electrical circuit in the Foster/Tank and Cauer/Filter configurations are included.

Note:

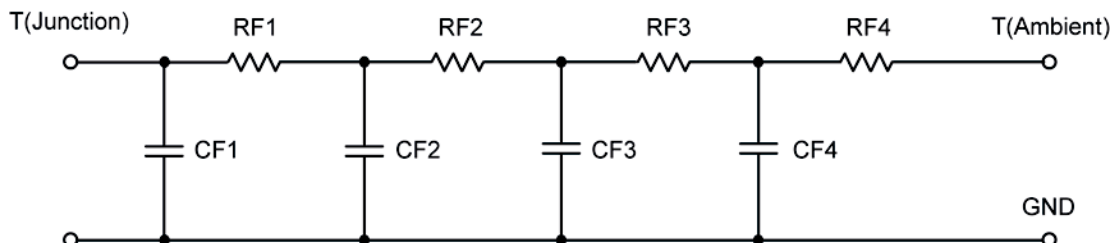
For a detailed explanation of implementing these values in P-SPICE, refer to [Application Note AN609 Thermal Simulations Of Power MOSFETs on P-SPICE Platform](#).

R-C THERMAL MODEL FOR TANK CONFIGURATION



| R-C VALUES FOR TANK CONFIGURATION | | | |
|--|------------|------|------|
| Thermal Resistance (°C/W) | | | |
| Junction to | Ambient | Case | Foot |
| RT1 | 49.6682 | N/A | N/A |
| RT2 | 43.5984 | N/A | N/A |
| RT3 | 57.2324 | N/A | N/A |
| RT4 | 15.5010 | N/A | N/A |
| Thermal Capacitance (Joules/°C) | | | |
| Junction to | Ambient | Case | Foot |
| CT1 | 2.1169 | N/A | N/A |
| CT2 | 32.2783 m | N/A | N/A |
| CT3 | 3.0813 m | N/A | N/A |
| CT4 | 144.6510 u | N/A | N/A |

This document is intended as a SPICE modeling guideline and does not constitute a commercial product data sheet. Designers should refer to the appropriate data sheet of the same number for guaranteed specification limits.

R-C THERMAL MODEL FOR FILTER CONFIGURATION**R-C VALUES FOR FILTER CONFIGURATION**

| Thermal Resistance ($^{\circ}\text{C}/\text{W}$) | | | |
|--|----------------|------|------|
| Junction to | Ambient | Case | Foot |
| RF1 | 16.4904 | N/A | N/A |
| RF2 | 58.3334 | N/A | N/A |
| RF3 | 40.4606 | N/A | N/A |
| RF4 | 50.7156 | N/A | N/A |
| Thermal Capacitance (Joules/ $^{\circ}\text{C}$) | | | |
| Junction to | Ambient | Case | Foot |
| CF1 | 135.2079 μ | N/A | N/A |
| CF2 | 2.4113 m | N/A | N/A |
| CF3 | 20.7337 m | N/A | N/A |
| CF4 | 1.9553 | N/A | N/A |

Note: NA indicates not applicable

Reference:

[1] "A Simple Method of Generating Thermal Models for a Power MOSFET" by Wharton McDaniel and Kandarp Pandya. IEEE / SEMITHERM 2002

